# PSMN5R5-60YS



# N-channel LFPAK 60 V, 5.2 m $\Omega$ standard level FET

Rev. 02 — 24 December 2009

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	60	V
$I_D$	drain current	T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	130	W
Tj	junction temperature			-55	-	175	°C
Avalanci	he ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 Ω; unclamped		-	-	170	mJ
Dynamic	characteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$		-	11.2	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}$ ; see Figure 14 and 15		-	56	-	nC



### N-channel LFPAK 60 V, 5.2 m $\Omega$ standard level FET

Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cl	haracteristics					
Doon	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	-	-	8.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	-	3.6	5.2	mΩ

<sup>[1]</sup> Continuous current is limited by package.

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate	9	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 Ś
			SOT669 (LFPAK)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R5-60YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

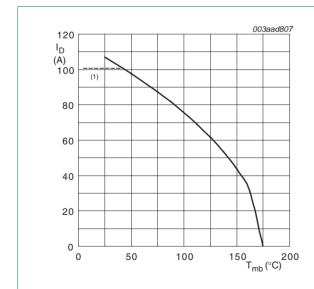
## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>		-	74	Α
		T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	418	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	130	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dr	ain diode					
I <sub>S</sub>	source current	$T_{mb} = 25  ^{\circ}C;$	<u>[1]</u>	-	100	Α
I <sub>SM</sub>	peak source current	t <sub>p</sub> ≤ 10 μs; pulsed; T <sub>mb</sub> = 25 °C		-	418	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 Ω; unclamped		-	170	mJ

#### [1] Continuous current is limited by package.



 $V_{\it GS} \ge 10$  V; (1) capped at 100 A due to package Fig 1. Continuous drain current as a function of

mounting base temperature

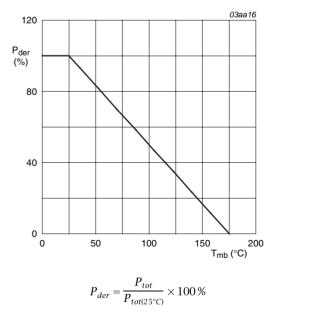
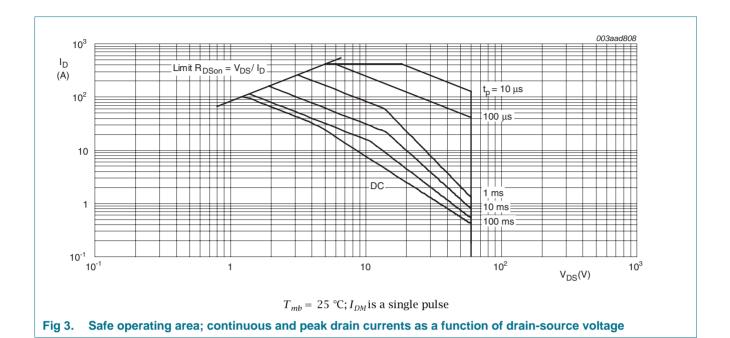


Fig 2. Normalized total power dissipation as a function of mounting base temperature



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## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.5	1.1	K/W

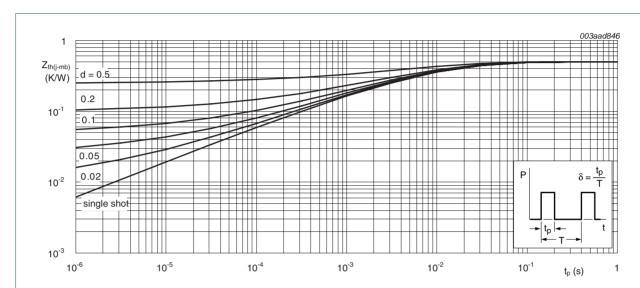


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub> drain-source		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; see <u>Figure 10</u> and <u>11</u>	2	3	4	V
$V_{GSth}$	th	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	4.6	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see Figure 11	0.95	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	5	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	7.6	12	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see <u>Figure 12</u>	-	-	8.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	3.6	5.2	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.7	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 75 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14 and 15	-	56	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	47.5	-	nC
$Q_{GS}$	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	18.7	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 75 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14	-	10.3	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	8.4	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 75 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14 and 15	-	11.2	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$V_{DS} = 30 \text{ V}$ ; see <u>Figure 14</u> and <u>15</u>	-	4.9	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	3501	-	pF
C <sub>oss</sub>	output capacitance	see Figure 16	-	457	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	240	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 0.4 \Omega; V_{GS} = 10 \text{ V};$	-	23	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	24	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	44	-	ns
t <sub>f</sub>	fall time		_	14	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 17</u>	-	8.0	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	43	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}$	-	58	-	nC

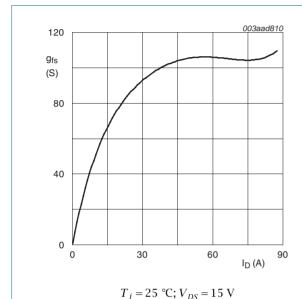
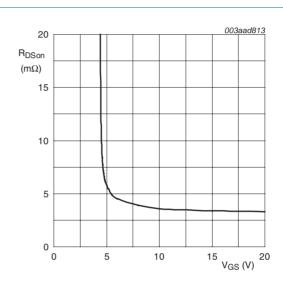


Fig 5. Forward transconductance as a function of drain current; typical values



 $T_i = 25$  °C;  $I_D = 25$  A

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

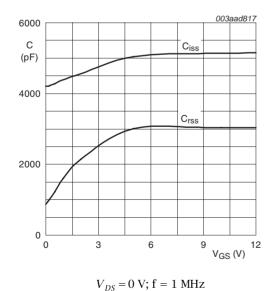


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

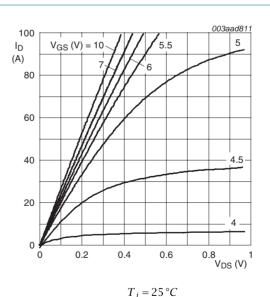
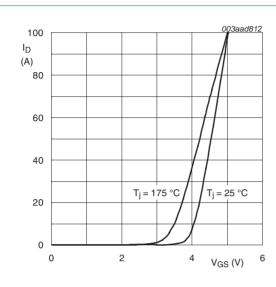
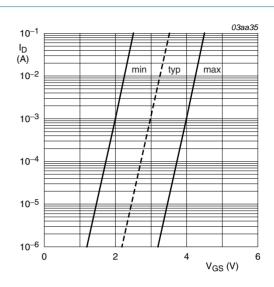


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



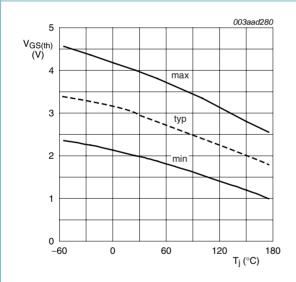
 $V_{DS} > I_D \times R_{DSon}$ 

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



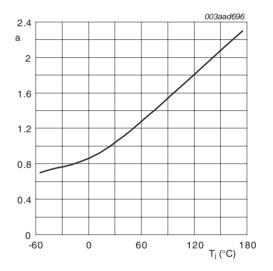
$$T_{j} = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



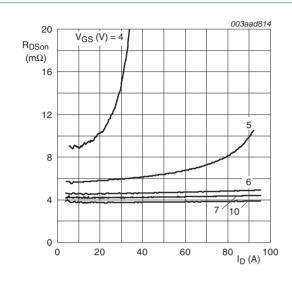
 $I_D = 1 \, mA; V_{DS} = V_{GS}$ 

Fig 11. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

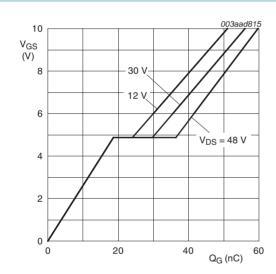


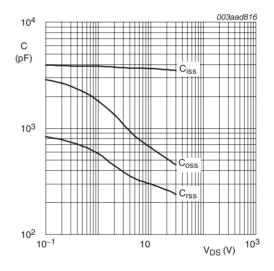
V<sub>GS</sub>(pl)
V<sub>GS</sub>(th)
V<sub>GS</sub>
Q<sub>GS1</sub> Q<sub>GS2</sub>
Q<sub>G</sub>(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}C$ 

Fig 14. Gate charge waveform definitions





 $T_J = 25$  °C;  $I_D = 75$  A

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

values

 $V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

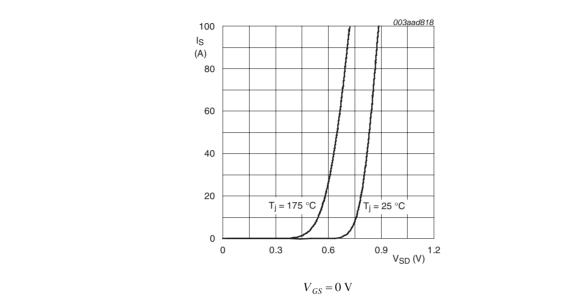


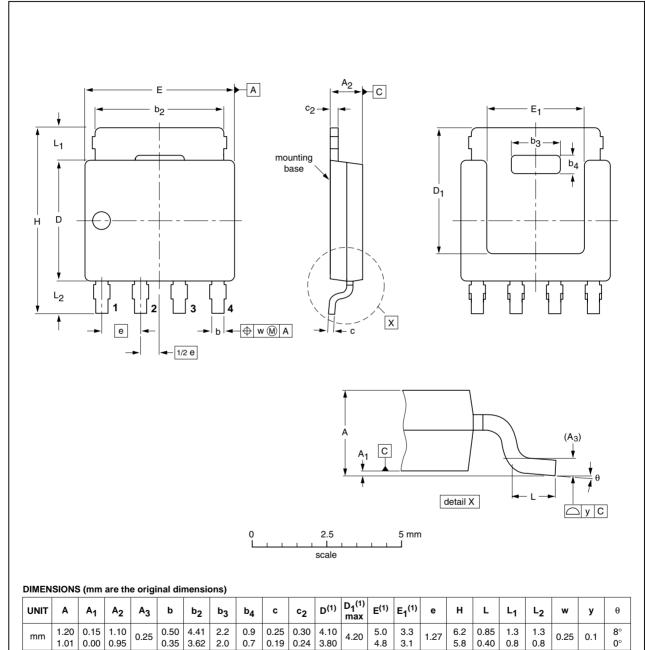
Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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## 7. Package outline

### Plastic single-ended surface-mounted package (LFPAK); 4 leads

**SOT669** 



#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EC JEITA		PROJECTION	ISSUE DATE	
SOT669		MO-235				<del>04-10-13</del> 06-03-16	

Fig 18. Package outline SOT669 (LFPAK)

## N-channel LFPAK 60 V, 5.2 m $\Omega$ standard level FET

## 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN5R5-60YS_2	20091224	Product data sheet	-	PSMN5R5-60YS_1	
Modifications:  • Status changed from objective to product.					
PSMN5R5-60YS_1	20091201	Objective data sheet	-	-	

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# **PSMN5R5-60YS**

## N-channel LFPAK 60 V, 5.2 m $\Omega$ standard level FET

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